

CHAPTER ONE

*Properties of Digital
Integrated Ccts.*

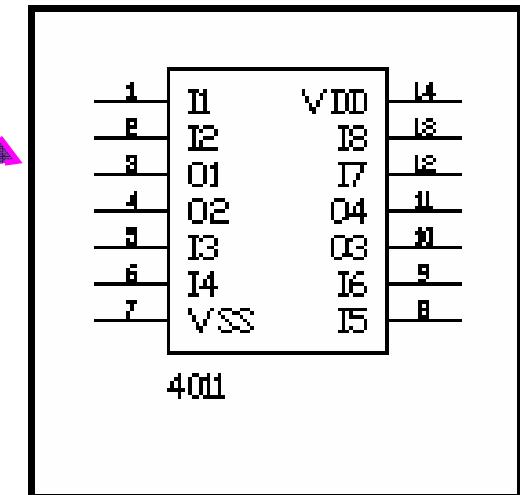
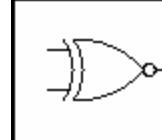
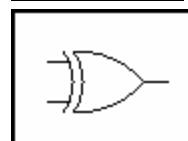
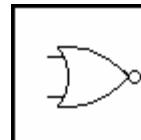
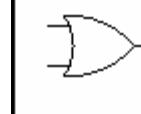
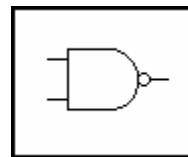
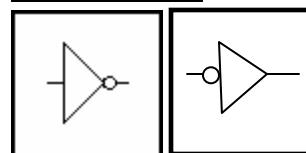
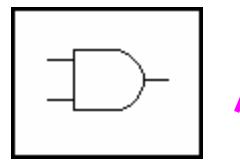
Digital Electronics.

Basic Logic Operations

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- AND
- NOT
- NAND
- OR
- NOR
- XOR
- XNOR



4 2-in AND



4 inputs with
two AND gates

Basic Logic Operations

- Combinational logic:

Output depends only on present value of the input.

- Sequential logic:

Output depends on present/past value of the input.

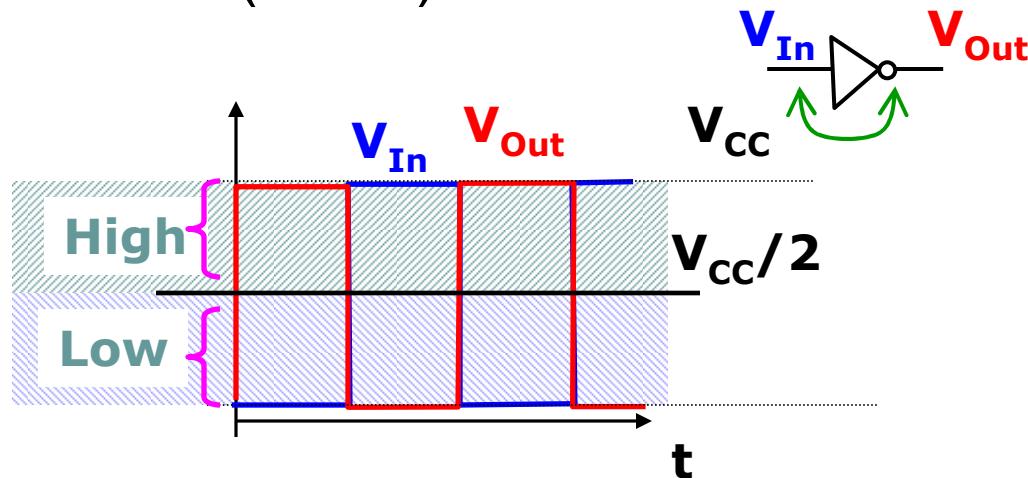
Basic Logic Operations

- The voltages/currents in digital logic circuits have two possible states (*according to positive voltage logic*) ✓:
 - Low voltage corresponds to a binary 0
 - High voltage corresponds to a binary 1
- *But according to negative voltage logic:*
 - Low voltage corresponds to a binary 1
 - High voltage corresponds to a binary 0

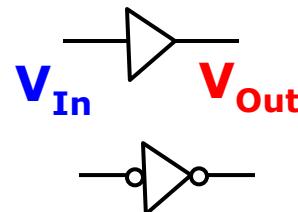
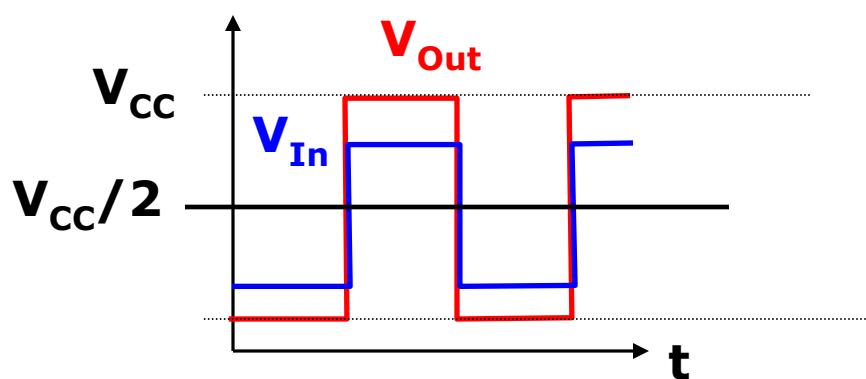
Basic Building Blocks

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- Inverter (NOT)



- Non-inverter (Buffer)



Used to regenerate voltage levels by making **degraded high levels higher** and **degraded low levels lower**

Voltage Transfer Characteristics (VTC) of Inverters

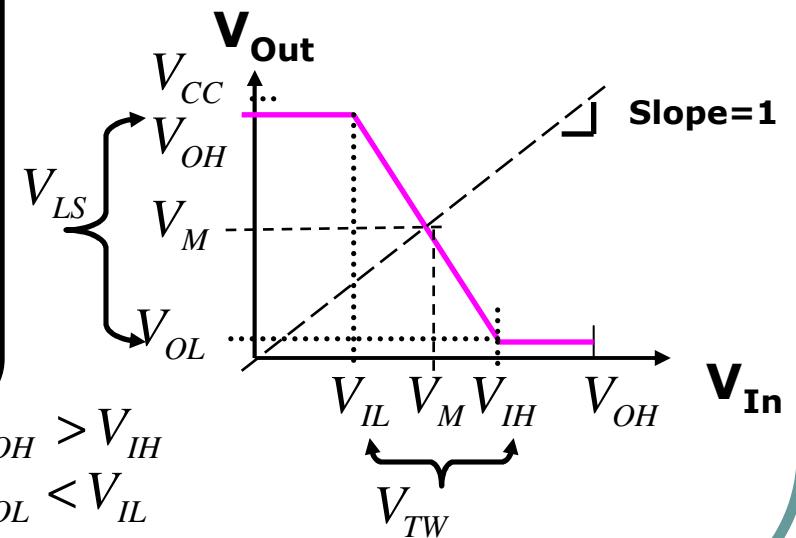
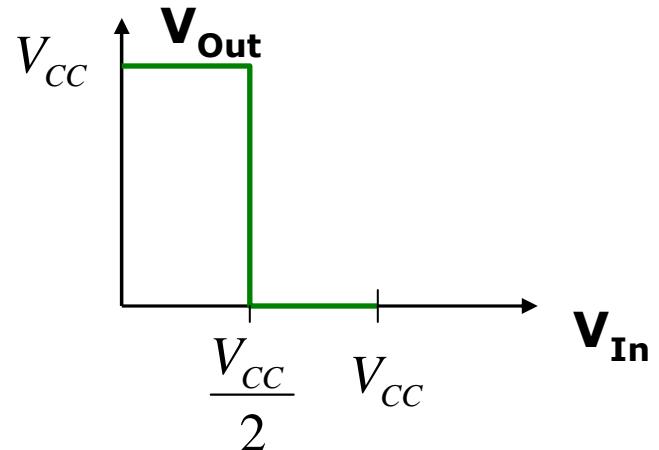
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- Ideal

- Practical

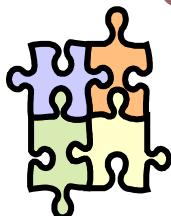
1. V_{OH} : Output high voltage level
2. V_{OL} : Output low voltage level
3. V_{IL} : Max. Input voltage that provides high output voltage
4. V_{IH} : Min. Input voltage that provides low output voltage
5. V_M : Midpoint ($V_{Out} = V_{In}$) ideally $\sim V_{CC}/2$
6. V_{LS} : Logic swing voltage. change in input to cause a change in output
7. V_{TW} : Transition width

The outputs of present inverter will be inputs to the next gate, "Low and High levels must be distinguishable"



Voltage Transfer Characteristics (VTC) of Inverters

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- Example

Assume $V_{OH} = 4.3$ V, $V_{OL} = 0.2$ V, $V_{IL} = 0.7$ V, $V_{IH} = 0.9$ V

Calculate V_{LS} , V_{TW} , and V_M

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- Solution

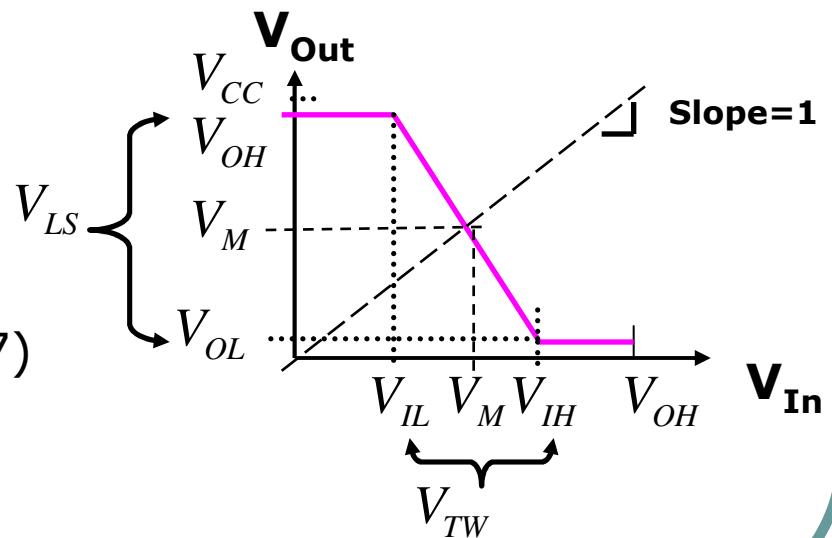
$$V_{LS} = 4.1 \text{ V},$$
$$V_{TW} = 0.2 \text{ V},$$

$$Y - y_0 = \text{slope}(x - x_0)$$

$$Y - 4.3 = [(0.2 - 4.3) / (0.9 - 0.7)](x - 0.7)$$

$$Y == x \rightarrow y = 0.867 \text{ V}$$

$$\rightarrow V_M = 0.867 \text{ V} \quad \text{far from } V_{CC}/2$$



Noise in Digital Ccts.

- Noise: Fluctuations (variations, degradations) of the steady state voltage levels
- Noise margins:
 - Low noise margin
 - High noise margin
- Noise Sensitivities:
 - Low noise sensitivity
 - High noise sensitivity
- Noise Immunities (ability of V_{gate} to reject noise)
 - Low noise immunity

$$V_{NML} = V_{IL} - V_{OL}$$

$$V_{NMH} = V_{OH} - V_{IH}$$

$$V_{NSL} = V_M - V_{OL}$$

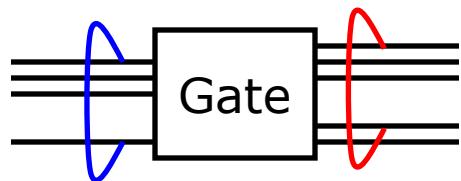
$$V_{NSH} = V_{OH} - V_M$$

Safety margins
(have to be positive)

Fan-In and Fan-Out

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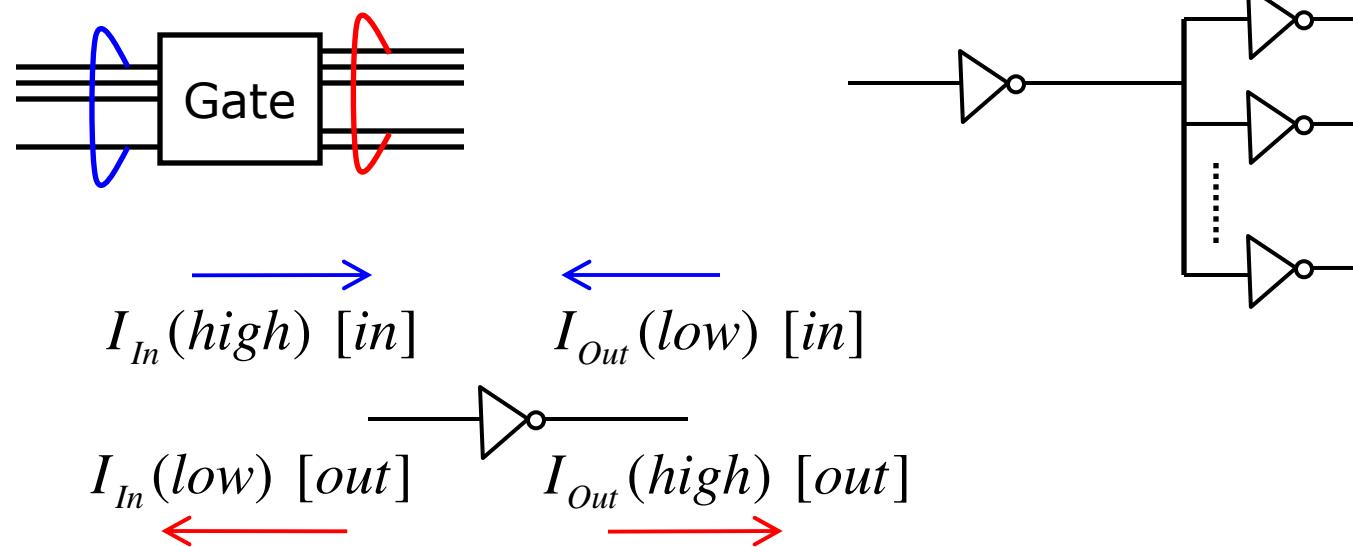


- Fan-In: (less concern)
Number of inputs of a gate.
- Fan-Out:
Number of outputs of a gate.

Maximum Fan-Out of a Digital Gate

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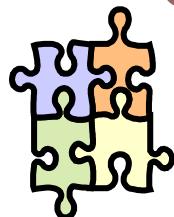


- Maximum Fan-out= $\min\{N_{low}, N_{high}\}$

$$N_{low} = \frac{I_{Out}(low)}{I_{In}(low)}$$

$$N_{high} = \frac{I_{Out}(high)}{I_{In}(high)}$$

Maximum Fan-Out of a Digital Gate



- **Example**

Assume

$$I_{In}(\text{high}) = 98.9 \mu\text{A}$$

$$I_{In}(\text{low}) = 2.43 \text{ mA}$$

$$I_{Out}(\text{high}) = 71.4 \text{ mA}$$

$$I_{Out}(\text{low}) = 54.3 \text{ mA}$$

Calculate the maximum fan-out.

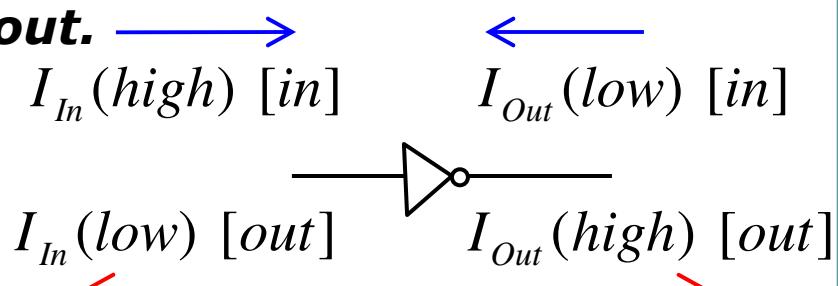
- **Solution**

$$N_{low} = \frac{I_{Out}(\text{low})}{I_{In}(\text{low})} = \frac{54.3}{2.43} = 22.3$$

$$N_{high} = \frac{I_{Out}(\text{high})}{I_{In}(\text{high})} = \frac{71.4}{0.0989} = 721.9$$



maximum fan-out = 22



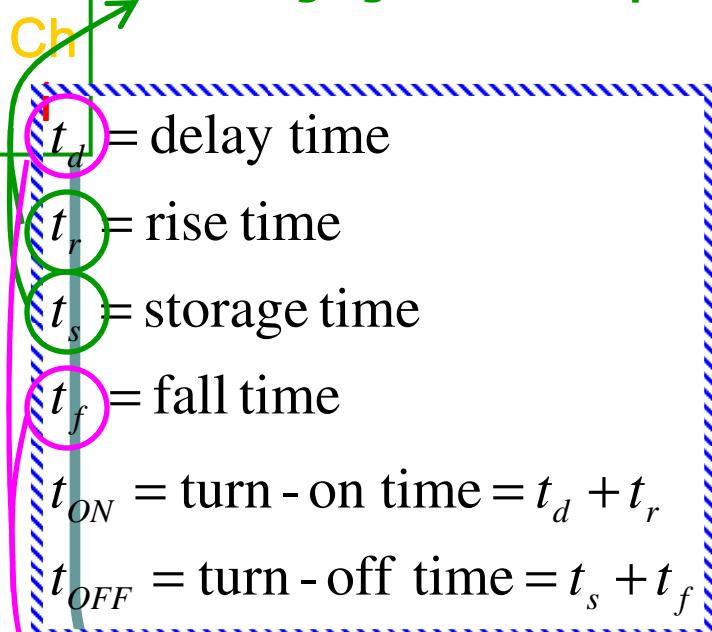
*Rounded to the
nearest lowest integer*

Transient Characteristics

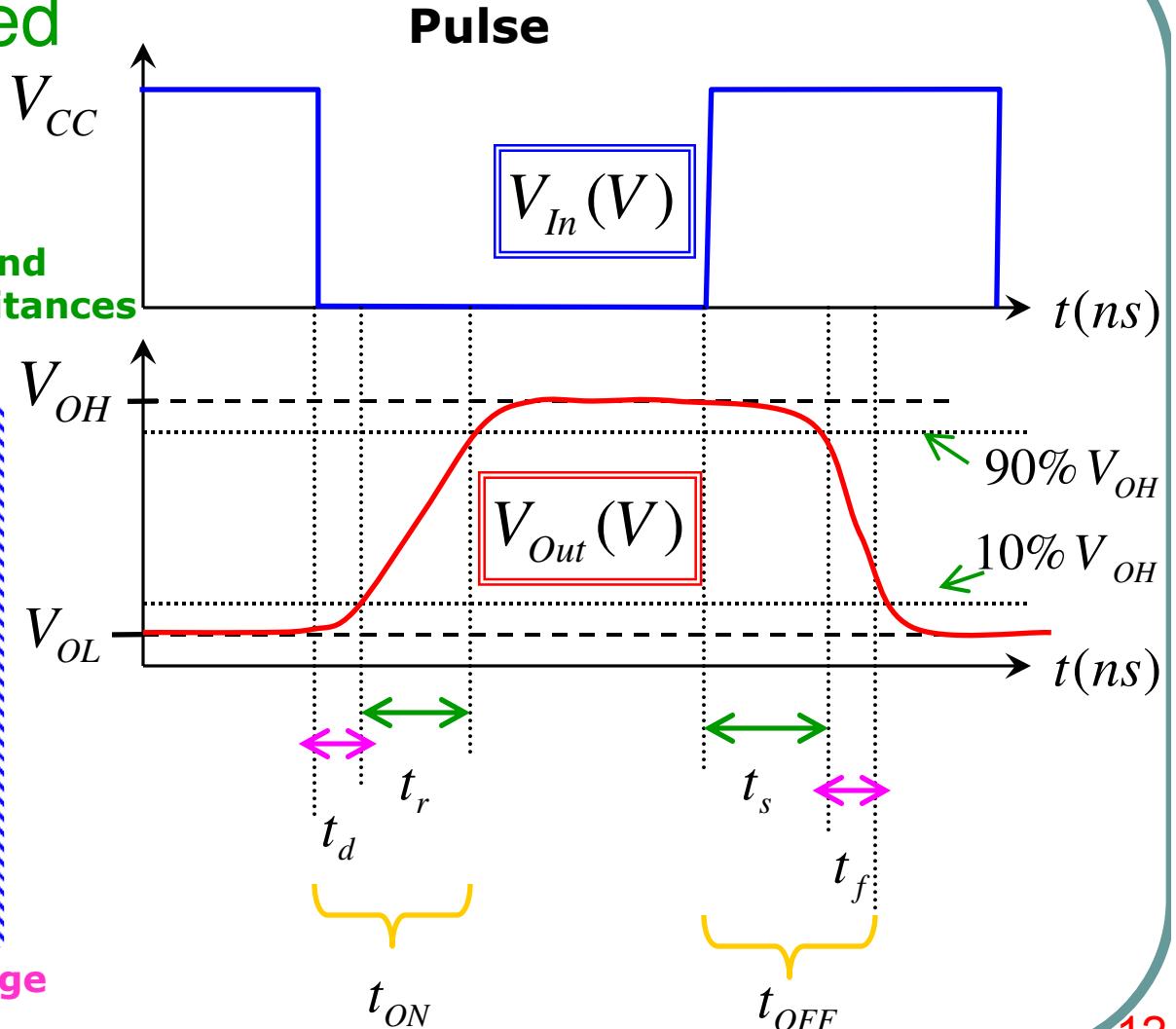
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- Switching speed

Associated with charging and discharging the load capacitances



Associated with stored charge of pn junction



Transient Characteristics

- Switching voltage high  low requires a finite amount of time, i.e., the output does not respond immediately (delay).
- *Propagation delay time (PDT)*: is the time interval between the application of an input and the response of the resulting output.
- In **BJTs**, PDT is caused by the time required to store and remove the charge from the **base region**.
- In **MOSFETs**, PDT is caused by the **metal oxide capacitance**

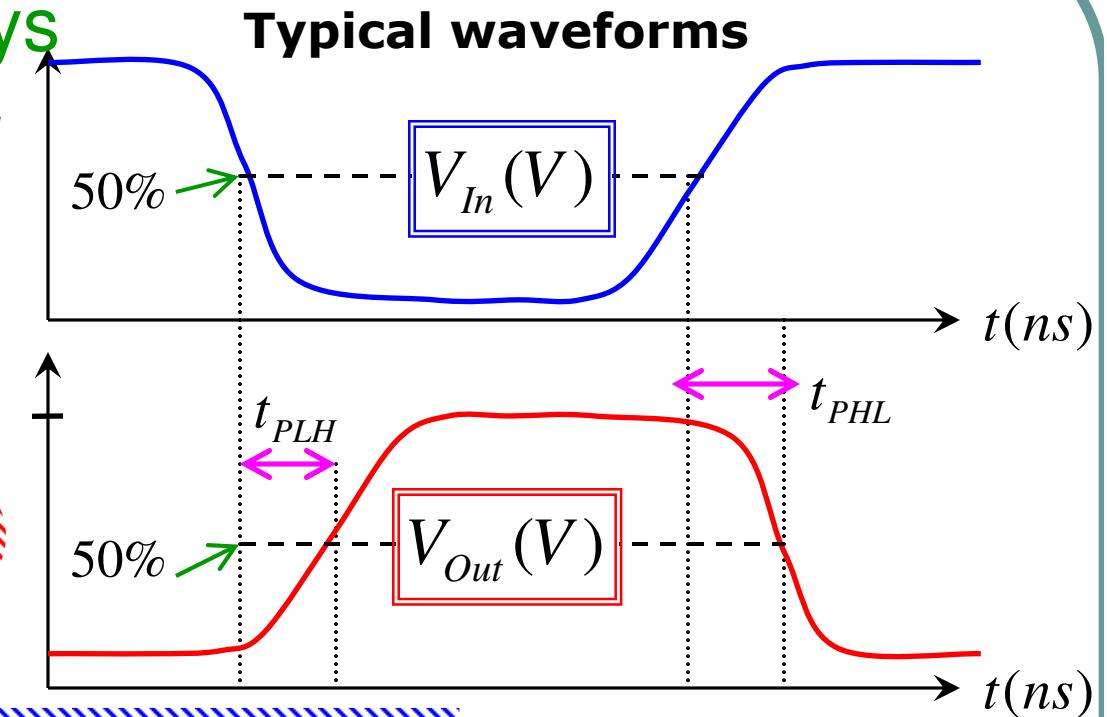
Transient Characteristics

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- Propagation delays

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The 50% points are used to define the time required for the output to respond



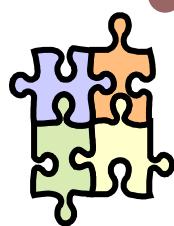
t_{PLH} = refers to low - to - high transition of the output

t_{PHL} = refers to high - to - low transition of the output

$$t_p(\text{avg}) = \frac{t_{PLH} + t_{PHL}}{2}$$

Transient Characteristics

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- **Example**

See example **1.5** on page 9

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Transient Characteristics

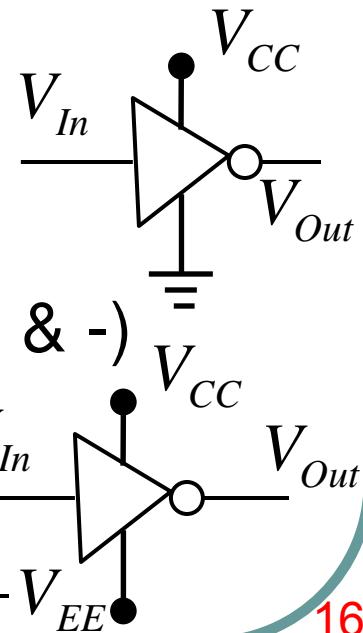
- **Power dissipation:**

- An ideal gate has a single power supply
- The power dissipated equals the power supplied
- The dissipated power in logic high and logic low states may differ

$$\begin{aligned}P_{CC}(\text{avg}) &= \frac{P_{CC}(\text{OH}) + P_{CC}(\text{OL})}{2} \\&= \left(\frac{I_{CC}(\text{OH}) + I_{CC}(\text{OL})}{2} \right) V_{CC}\end{aligned}$$

- Some gates have two power supplies (+ & -)

$$\begin{aligned}P_{DISS}(\text{avg}) &= P_{CC}(\text{avg}) + P_{EE}(\text{avg}) \\&= \left(\frac{I_{CC}(\text{OH}) + I_{CC}(\text{OL})}{2} \right) V_{CC} + \left(\frac{I_{EE}(\text{OH}) + I_{EE}(\text{OL})}{2} \right) V_{EE}\end{aligned}$$



Transient Characteristics

- Power-Delay product (*speed-power product*):
 - Low power dissipation and short propagation delay are desirable for digital ICs.
 - But, faster propagation delay times are achieved at the cost of increased power dissipation.
 - As a figure of merit, power-delay product is defined as
- $$PD = P_{DISS}(\text{avg}) \times t_p(\text{avg}) \text{ [J]: joules}$$
- The smaller the PD is, the more ideal the gate is.
Ideally $PD=0$ J.

Assignment # 1

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- HW #1: Solve Problems: 1.1, 1.5, 1.12, 1.22, and 1.24